A FET Amplifier in Fin-Line Technique

J. L'Ecuyer, G.B. Gajda and W.J.R. Hoefer. "A FET Amplifier in Fin-Line Technique." 1986 MTT-S International Microwave Symposium Digest 86.1 (1986 [MWSYM]): 287-290.

This paper describes the successful demonstration of a stable FET amplifier using fin-line technique. The circuit has been realized in integrated E-plane technology, utilizing two main fin-line ports and a microstrip/coplanar bias circuit. The amplifier was designed for 17 GHz operation using a NE67300 FET and achieved a gain of 6 dB over a bandwidth of 1 GHz.

❑ Return to main document.